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ABSTRACT OF THE DISCLOSURE

Method for Manufacturing Group III-V Compound Semiconductor

A method for manufacturing a group III-V compound semiconductor represented by the general formula $\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$ (where $x+y+z = 1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, and $0 \leq z \leq 1$) by metalorganic vapor phase epitaxy method is provided. The group III-V compound semiconductor has a semiconductor layer consisting of a p-type dopant-nondoped layer, and a semiconductor layer including a p-type dopant-doped layer. In the method, a reactor for growing the semiconductor layer consisting of a p-type dopant-nondoped layer and a reactor for doping a p-type dopant are mutually different. (Figure 3)



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